

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A thin-film semiconductor device comprising:
a first plurality of thin-film transistors having different driving voltages than a second plurality of thin-film transistors, wherein said first and second plurality of transistors are formed on a glass substrate,
wherein an electric field of a gate ~~electrode~~ insulator at each of said driving voltages of said first and second plurality of thin-film transistors is in a range of about 1MV/cm to 2MV/cm, and a drain concentration of P-type thin-film transistors is in a range of about $3E+19/cm^3$ to $1E+20/cm^3$.
2. (original): The thin-film semiconductor device according to claim 1, wherein said first plurality of thin-film transistors comprising N-type and P-type thin-film transistors have a lower driving voltage than said second plurality of thin-film transistors comprising N-type and P-type thin film transistor.
3. (original): The thin-film semiconductor device according to claim 1, wherein a plurality of gate insulating films of said first and second plurality of thin-film transistors have substantially the same thickness.

4. (original): The thin-film semiconductor device according to claim 2,
wherein at least one N-type thin-film transistor of said second plurality of thin-film
transistors have a lightly-doped drain structure.

5. (currently amended): A thin-film semiconductor device comprising:
a first plurality of thin-film transistors having different driving voltages than a second
plurality of thin-film transistors, wherein said first and second plurality of transistors are formed
on a glass substrate,

wherein an electric field of a gate electrode insulator at each of said driving voltages of
said first and second plurality of thin-film transistors is in a range of about 0.2MV/cm to
0.8MV/cm, and a drain concentration of P-type thin-film transistors is in a range of about
 $3E+19/cm^3$ to $1E+20/cm^3$.

6. (original): The thin-film semiconductor device according to claim 5,
wherein said first and second plurality of thin-film transistors comprising N-type and P-
type thin-film transistors have a lower driving voltage than said second plurality of thin-film
transistors comprising N-type and P-type thin film transistor.

7. (original): The thin-film semiconductor device according to claim 5,
wherein a plurality of gate insulating films of said first and second plurality of thin-film
transistors has substantially the same thickness.

8. (original): The thin-film semiconductor device according to claim 6,
wherein at least one N-type thin-film transistor of said second plurality of thin-film
transistors have a lightly-doped drain structure.

Claims 9-12 (canceled).

13. (original): A liquid crystal display comprising:
a thin-film semiconductor device according to claim 1; and
a driver circuit.

Claim 14 (canceled).

15. (withdrawn): A thin-film semiconductor device manufacturing method
comprising:
providing a glass substrate
forming a plurality of gate insulating films of a plurality of thin-film transistors, wherein
said gate insulating films are formed so as to have a substantially the same thickness, and
wherein said plurality of thin-film transistors have different driving voltages.

16. (withdrawn): The thin-film semiconductor device manufacturing method
according to claim 15,
wherein said gate insulating films are formed at substantially the same time.

17. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 15, further comprising:

forming source/drain regions of a plurality of P-type thin-film transistors having different driving voltages.

18. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 15, further comprising:

forming source/drain regions of a plurality of N-type thin-film transistors having different driving voltages.

19. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 17, wherein said source/drain regions are formed at substantially the same time.

20. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 18,

wherein said source/drain regions are formed at substantially the same time.

21. (withdrawn): The thin-film semiconductor device manufacturing method according to claim 18, further comprising:

forming Lightly-doped drain structure on at least one part of the N-type thin-film transistors.